

2STW4466

High power NPN epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = 80 V
- Complementary to 2STW1693
- Typical f_t = 20 MHz
- Fully characterized at 125 °C

Applications

■ Audio power amplifier

Description

The device is a NPN transistor manufactured in low voltage planar technology using base island layout. The resulting transistor shows good gain linearity coupled with low $V_{CE(sat)}$ behaviour. Recommended for 40 W to 70 W high fidelity audio frequency amplifier output stage.

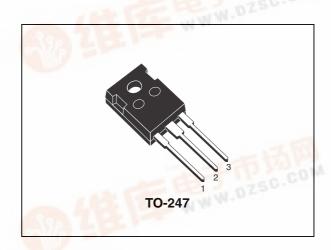


Figure 1. Internal schematic diagram

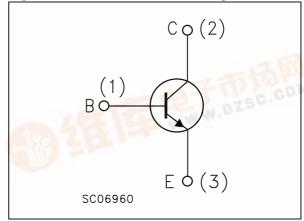


Table 1. Device summary

Order code Marking		Package	Packaging	
2STW4466 2STW4466 TO-247 Tub		Tube		
@维库	WWW.DZSC.COM			

Electrical ratings 2STW4466

1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage (I _E = 0)	100	V
V_{CEO}	Collector-emitter voltage (I _B = 0)	80	٧
V_{EBO}	Emitter-base voltage (I _C = 0)	6	V
I _C	Collector current	6	Α
I _{CM}	Collector peak current (t _P < 5 ms)	12	Α
P _{TOT}	Total dissipation at T _c = 25 °C	60	W
T _{stg}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	2.08	°C/W

2STW4466 Electrical characteristics

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C; unless otherwise specified)$

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 100 V				0.1	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 6 V				0.1	μΑ
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C = 0)	I _E = 1 mA		6			V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = 100 μA		100			V
V _{(BR)CEO}	Collector-emitter breakdown voltage (I _B = 0)	I _C = 50 mA		80			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = 2$ $I_C = 6 \text{ A}$	$I_B = 200 \text{ mA}$ $I_B = 600 \text{ mA}$			0.6 1.5	> >
V _{BE} (1)	Base-emitter voltage	V _{CE} = 4 V	I _C = 6 A			1.5	V
h _{FE}	DC current gain	I _C = 2 A	V _{CE} = 4 V	50		120	
f _T	Transition frequency	I _C = 0.5 A	V _{CE} = 12 V		20		MHz
C _{CBO}	Collector-base capacitance (I _E = 0)	V _{CB} = 10 V	f = 1 MHz		50		pF
	Resistive load						
t _{on}	Turn-on time	$I_C = 3 A$	$V_{CC} = 30 \text{ V}$		0.15		ns
t _{stg}	Storage time	$I_{B1} = -I_{B2} = 0.3 A$	A		1.5		ns
t _f	Fall time				0.1		ns

Pulsed duration = 300 μ s, duty cycle $\leq 1.5\%$

Electrical characteristics 2STW4466

2.1 Electrical characteristics (curves)

Figure 2. DC current gain

Figure 3. DC current gain

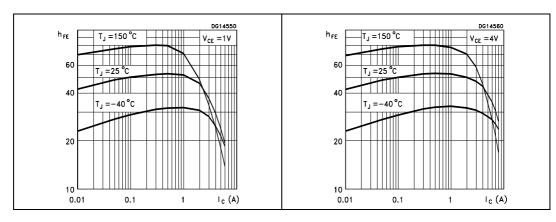


Figure 4. Collector-emitter saturation voltage

Figure 5. Base-emitter saturation voltage

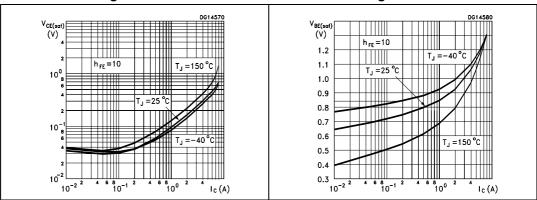
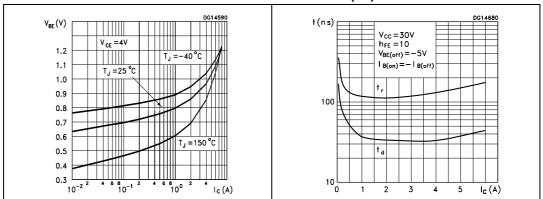


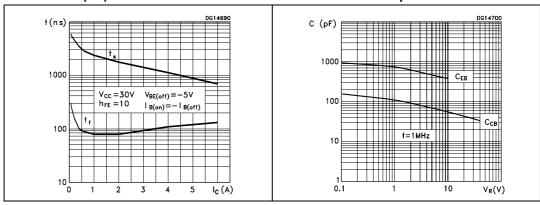
Figure 6. Base emitter voltage

Figure 7. Resistive load switching time (on)



2STW4466 Electrical characteristics

Figure 8. Resistive load switching time Figure 9. Emitter-base and collector-(off) base capacitance



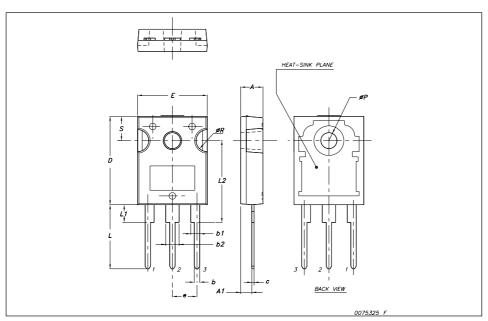
Package mechanical data 2STW4466

3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-247 Mechanical data

Dim.	mm.				
Dilli.	Min.	Тур	Max.		
Α	4.85		5.15		
A1	2.20		2.60		
b	1.0		1.40		
b1	2.0		2.40		
b2	3.0		3.40		
С	0.40		0.80		
D	19.85		20.15		
E	15.45		15.75		
е		5.45			
L	14.20		14.80		
L1	3.70		4.30		
L2		18.50			
øΡ	3.55		3.65		
øR	4.50		5.50		
S		5.50			



Revision history 2STW4466

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
11-Oct-2007	1	First release
25-Sep-2008	2	Content reworked to improve readability, no technical changes.

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